

RD74LVC00B

Quad. 2-input NAND Gates

REJ03D0222-0100Z Rev.1.00 May 11, 2004

Description

The RD74LVC00B has four 2-input NAND gates in a 14 pin package. Low voltage and high speed operation is suitable at the battery drive product (note type personal computer) and low power consumption extends the life of a battery for long time operation.

Features

- $V_{CC} = 1.65 \text{ V to } 5.5 \text{ V}$
- All inputs V_{IH} (Max.) = 5.5 V (@ V_{CC} = 0 V to 5.5 V)
- Typical V_{OL} ground bounce < 0.8 V (@ V_{CC} = 3.3 V, Ta = 25°C)
- Typical V_{OH} undershoot > 2.0 V (@ V_{CC} = 3.3 V, Ta = 25°C)
- High output current $\pm 4 \text{ mA } (@V_{CC} = 1.65 \text{ V})$

 $\pm 8 \text{ mA } (@V_{CC} = 2.3 \text{ V})$

 $\pm 12 \text{ mA } (@V_{CC} = 2.7 \text{ V})$

 ± 24 mA (@V_{CC} = 3.0 V to 5.5 V)

Ordering Information

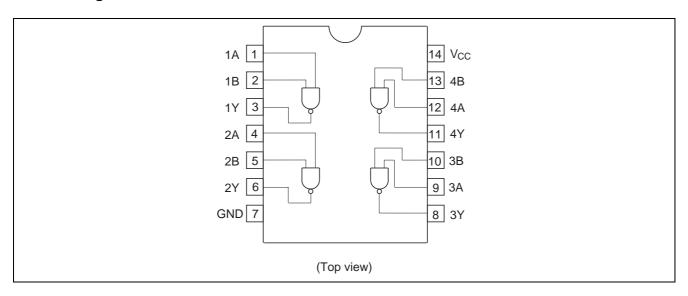
Part Name	rt Name Package Type		Package Abbreviation	Taping Abbreviation (Quantity)	
RD74LVC00BFPEL	SOP-14 pin (JEITA)	FP-14DAV	FP	EL (2,000 pcs/reel)	
RD74LVC00BTELL	TSSOP-14 pin	TTP-14DV	T	ELL (2,000 pcs/reel)	

Function Table

		Inputs	COM				
	Α	P.W.DZSU.	В	Output Y			
L	20 4 EE 15 15 15 15 15 15 15 15 15 15 15 15 15	At As a		Н			
L		Н		Н			
Н	The second second	L		H			
Н		Н		L CC COM			
H:	High level Low level		e thi	W.W.W.DZS			
L:	Low level						



Pin Arrangement



Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Conditions		
Supply voltage	oply voltage V _{CC} -0.5		V			
Input diode current	I _{IK}	-50	mA	V _I = -0.5 V		
Input voltage	Vi	-0.5 to 7.0	V			
Output diode current	I _{OK}	-50	mA	$V_0 = -0.5 \text{ V}$		
		50	mA	$V_{O} = V_{CC} + 0.5 \text{ V}$		
Output voltage	Vo	-0.5 to V _{CC} +0.5	V			
Output current	Io	±50	mA			
V _{CC} , GND current / pin	I _{CC} or I _{GND}	100	mA			
Storage temperature	Tstg	-65 to +150	°C			

Note: The absolute maximum ratings are values, which must not individually be exceeded, and furthermore, no two of which may be realized at the same time.

Recommended Operating Conditions

Item	Symbol	Ratings	Unit	Conditions
Supply voltage	V _{CC}	1.5 to 5.5	V	Data hold
		1.65 to 5.5		At operation
Input / Output voltage	Vı	0 to 5.5	V	A, B
	Vo	0 to V _{CC}		Υ
Operating temperature	Та	-40 to 85	°C	
Output current	I _{OH}	-4	mA	V _{CC} = 1.65 V
		-8		V _{CC} = 2.3 V
		-12		V _{CC} = 2.7 V
		-24		V _{CC} = 3.0 V to 5.5 V
	I _{OL}	4		V _{CC} = 1.65 V
		8		V _{CC} = 2.3 V
		12		V _{CC} = 2.7 V
		24		$V_{CC} = 3.0 \text{ V to } 5.5 \text{ V}$
Input rise / fall time*1	t _r , t _f	20	ns/V	V _{CC} = 1.65 V to 2.7 V
		10		$V_{CC} = 3.0 \text{ V to } 5.5 \text{ V}$

Notes: 1. This item guarantees maximum limit when one input switches.

Waveform: Refer to test circuit of switching characteristics.

Electrical Characteristics

	Ta = -40 to 85°C								
Item	Symbol	V _{CC} (V)	Min	Max	Unit	Test Conditions			
Input voltage	V _{IH}	1.65 to 1.95	V _{CC} ×0.65		V				
		2.3 to 2.7	1.7	_					
		2.7 to 3.6	2.0	_					
		4.5 to 5.5	V _{CC} ×0.7	_					
	V _{IL}	1.65 to 1.95	_	V _{CC} ×0.35					
		2.3 to 2.7	_	0.7					
		2.7 to 3.6	_	0.8					
		4.5 to 5.5	_	V _{CC} ×0.3					
Output voltage	V _{OH}	1.65 to 5.5	V _{CC} -0.2	_	V	I _{OH} = -100 μA			
		1.65	1.2	_		$I_{OH} = -4 \text{ mA}$			
		2.3	1.7	_		I _{OH} = -8 mA			
		2.7	2.2	_		I _{OH} = -12 mA			
		3.0	2.4	_					
		3.0	2.2	_		I _{OH} = -24 mA			
		4.5	3.8						
	V_{OL}	1.65 to 5.5	_	0.2		I _{OL} = 100 μA			
		1.65	_	0.45		I _{OL} = 4 mA			
		2.3	_	0.7		I _{OL} = 8 mA			
		2.7	_	0.4		I _{OL} = 12 mA			
		3.0	_	0.55		$I_{OL} = 24 \text{ mA}$			
		4.5	_	0.55					
Input current	I _{IN}	0 to 5.5	_	±5.0	μΑ	V _{IN} = 5.5 V or GND			
Quiescent supply current	Icc	2.7 to 3.6	_	±5.0	μΑ	$V_{IN} = 3.6 \text{ V to } 5.5 \text{ V}$			
		2.7 to 5.5	_	5.0		$V_{IN} = V_{CC}$ or GND			
	ΔI_{CC}	2.7 to 3.6		500		V_{IN} = one input at (V_{CC} -0.6)V, other inputs at V_{CC} or GND			

Switching Characteristics

			Ta = -40 to 85°C				From	То
Item	Symbol	V _{CC} (V)	Min	Тур	Max	Unit	(Input)	(Output)
Propagation delay time	t _{PLH}	1.8±0.15	1.0	_	12.5	ns	A or B	Υ
	t _{PHL}	2.5±0.2	1.0	_	6.4			
		2.7	1.0	_	5.1			
		3.3±0.3	1.0	_	4.3			
		5.0±0.5	1.0	_	3.6			
Between output pins skew*1	t _{OSLH}	1.8±0.15	_	_	_	ns		
	toshl	2.5±0.2	_	_	_			
		2.7	_	_	_			
		3.3±0.3	_	_	1.0			
		5.0±0.5	_	_	1.0	1		
Input capacitance	C _{IN}	3.3	_	5.0	_	pF		

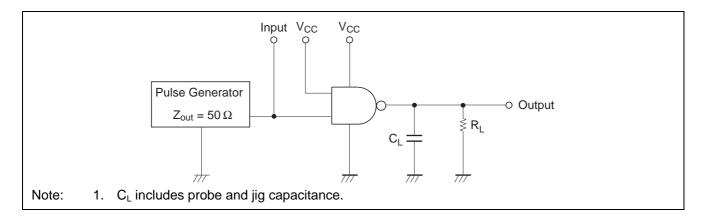
Note: 1. This parameter is characterized but not tested.

 $t_{\text{OSLH}} = \left|t_{\text{PLHm}} - t_{\text{PLHn}}\right|, \ t_{\text{OSHL}} = \left|t_{\text{PHLm}} - t_{\text{PHLn}}\right|$

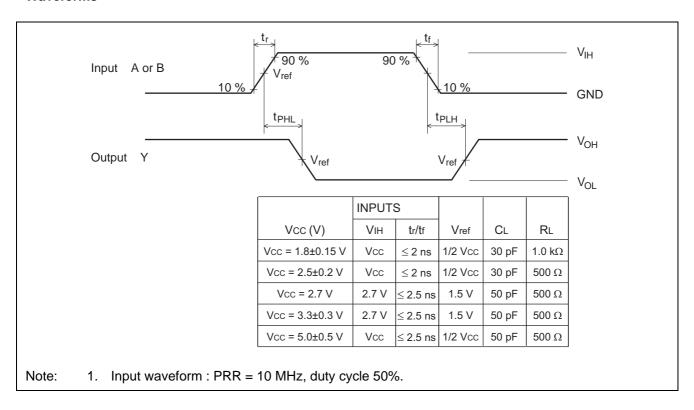
Operating Characteristics

			Ta = 25°C				
Item	Symbol	V _{CC} (V)	Min	Тур	Max	Unit	Test conditions
Power dissipation Capacitance	C _{PD}	1.8	_	10	_	pF	f = 10 MHz
		2.5	_	12	_		
		3.3	_	12	_		
		5.0	_	15	_		

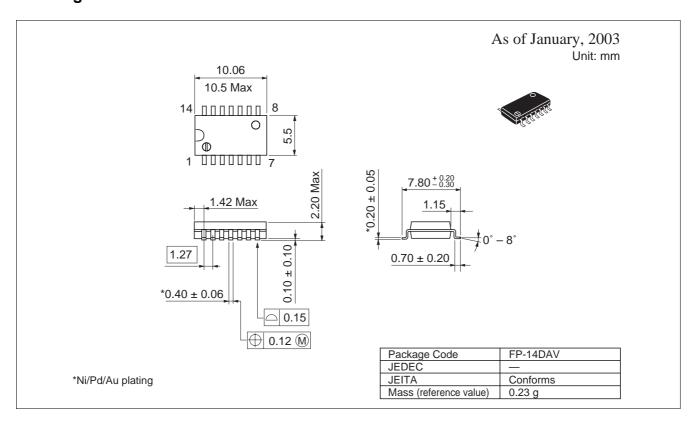
Test Circuit

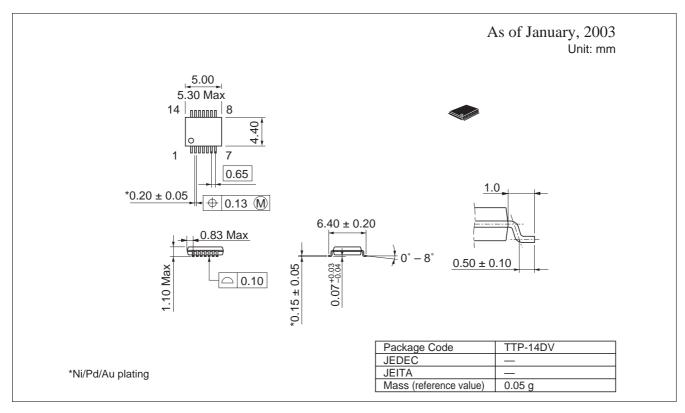


Waveforms



Package Dimensions





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